

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

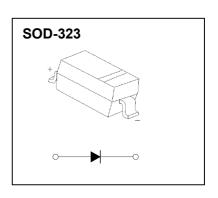
SOD-323 Plastic-Encapsulate Diodes

MA729 SWITCHING DIODE

FEATURES

- For Small Current Rectification
- For Super High Speed Switching
- High-density Mounting is Possible

MARKING: 2B



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{R}	DC Blocking Voltage	30	V
V_{RRM}	Repetitive Peak Reverse Voltage	30	V
I _F	Forward Current	200	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ 10ms half sine wave	1	Α
P _D	Power Dissipation	200	mW
R _{0JA}	Thermal Resistance from Junction to Ambient	500	°CW
Tj	Junction Temperature	125	℃
T _{stg}	Storage Temperature	-55~+150	$^{\circ}$

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

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Parameter	Symbol	Test conditions	Min	Тур	Max	Unit			
Reverse voltage	$V_{(BR)}$	I _R =100μA	30			V			
Reverse current	I _R	V _R =30V			50	μA			
Forward voltage	V _F	I _F =200mA			0.55	V			
Total capacitance	C _{tot}	V _R =0V,f=1MHz		30		pF			
Reverse recovery time	t _{rr}	$I_F = I_R = 100 \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$		3		ns			

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